

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

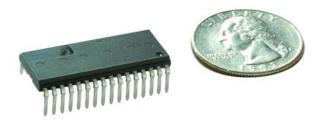
FSB50550U Smart Power Module (SPM[®])

Features

- 500V R_{DS(on)}=1.4Ω(max) 3-phase FRFET inverter including high voltage integrated circuit (HVIC)
- 3 divided negative dc-link terminals for inverter current sensing applications
- HVIC for gate driving and undervoltage protection
- 3/5V CMOS/TTL compatible, active-high interface
- Optimized for low electromagnetic interference
- Isolation voltage rating of 1500Vrms for 1min.

General Description

FSB50550U is a tiny smart power module (SPM[®]) based on FRFET technology as a compact inverter solution for small power motor drive applications such as fan motors and water suppliers. It is composed of 6 fast-recovery MOSFET (FRFET), and 3 half-bridge HVICs for FRFET gate driving. FSB50550U provides low electromagnetic interference (EMI) characteristics with optimized switching speed. Moreover, since it employs FRFET as a power switch, it has much better ruggedness and larger safe operation area (SOA) than that of an IGBT-based power module or one-chip solution. The package is optimized for the thermal performance and compactness for the use in the built-in motor application and any other application where the assembly space is concerned. FSB50550U is the most solution for the compact inverter providing the energy efficiency, compactness, and low electromagnetic interference.



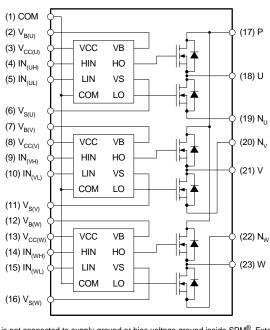
Absolute Maximum Ratings

Symbol	Parameter	Conditions	Rating	Units	
V _{PN}	DC Link Input Voltage, Drain-source Voltage of each FRFET		500	V	
I _{D25}	Each FRFET Drain Current, Continuous	$T_{C} = 25^{\circ}C$	2.0	А	
I _{D80}	Each FRFET Drain Current, Continuous	$T_{\rm C} = 80^{\circ}{\rm C}$	1.5	А	
I _{DP}	Each FRFET Drain Current, Peak	T _C = 25°C, PW < 100μs	5	А	
PD	Maximum Power Dissipation	T _C = 25°C, Each FRFET	14.5	W	
V _{CC}	Control Supply Voltage	Applied between V _{CC} and COM	20	V	
V _{BS}	High-side Bias Voltage	Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	20	V	
V _{IN}	Input Signal Voltage	Applied between IN and COM	-0.3 ~ VCC+0.3	V	
Τ _J	Operating Junction Temperature		-40 ~ 150	°C	
T _{STG}	Storage Temperature		-50 ~ 150	°C	
R_{\thetaJC}	Junction to Case Thermal Resistance Each FRFET under inverter dition (Note 1)		8.6	°C/W	
V _{ISO}	Isolation Voltage	60Hz, Sinusoidal, 1 minute, Connection pins to heatsink	1500	V _{rms}	

FSB50550U
Smart Power
r Module (
(SPM®)

Pin Descriptions

Pin Number	Pin Name	Pin Description	
1	СОМ	IC Common Supply Ground	
2	V _{B(U)}	Bias Voltage for U Phase High Side FRFET Driving	
3	V _{CC(U)}	Bias Voltage for U Phase IC and Low Side FRFET Driving	
4	IN _(UH)	Signal Input for U Phase High-side	
5	IN _(UL)	Signal Input for U Phase Low-side	
6	V _{S(U)}	Bias Voltage Ground for U Phase High Side FRFET Driving	
7	V _{B(V)}	Bias Voltage for V Phase High Side FRFET Driving	
8	V _{CC(V)}	Bias Voltage for V Phase IC and Low Side FRFET Driving	
9	IN _(VH)	Signal Input for V Phase High-side	
10	IN _(VL)	Signal Input for V Phase Low-side	
11	V _{S(V)}	Bias Voltage Ground for V Phase High Side FRFET Driving	
12	V _{B(W)}	Bias Voltage for W Phase High Side FRFET Driving	
13	V _{CC(W)}	Bias Voltage for W Phase IC and Low Side FRFET Driving	
14	IN _(WH)	Signal Input for W Phase High-side	
15	IN _(WL)	Signal Input for W Phase Low-side	
16	V _{S(W)}	Bias Voltage Ground for W Phase High Side FRFET Driving	
17	Р	Positive DC-Link Input	
18	U	Output for U Phase	
19	NU	Negative DC-Link Input for U Phase	
20	N _V	Negative DC-Link Input for V Phase	
21	V	Output for V Phase	
22	N _W	Negative DC–Link Input for W Phase	
23	W	Output for W Phase	



Note: Source terminal of each low-side MOSFET is not connected to supply ground or bias voltage ground inside SPM[®]. External connections should be made as indicated in Figure 2 and 5.

Figure 1. Pin Configuration and Internal Block Diagram (Bottom View)

Electrical Characteristics ($T_J = 25^{\circ}C$, $V_{CC} = V_{BS} = 15V$ Unless Otherwise Specified)

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions		Тур	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{IN} = 0V, I _D = 250μA (Note 2)		-	-	V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Tem- perature Coefficient	$I_D = 250\mu A$, Referenced to $25^{\circ}C$		0.53	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{IN} = 0V, V _{DS} = 500V	-	-	250	μΑ
R _{DS(on)}	Static Drain-Source On-Resistance	V _{CC} = V _{BS} = 15V, V _{IN} = 5V, I _D = 1.2A		1.0	1.4	Ω
V _{SD}	Drain-Source Diode Forward Voltage	$V_{CC} = V_{BS} = 15V, V_{IN} = 0V, I_D = -1.2A$		-	1.2	V
t _{ON}		$V_{PN} = 300V, V_{CC} = V_{BS} = 15V, I_D = 1.2A$ $V_{IN} = 0V \leftrightarrow 5V$	-	600	-	ns
t _{OFF}			-	500	-	ns
t _{rr}	Switching Times	Inductive load L=3mH High- and low-side FRFET switching	-	100	-	ns
E _{ON}			-	60	-	μJ
E _{OFF}		(Note 3)		10	-	μJ
RBSOA	Reverse-bias Safe Oper- ating Area	$ V_{PN} = 400V, V_{CC} = V_{BS} = 15V, I_D = I_{DP,} V_{DS} = BV_{DSS}, \\ T_J = 150^{\circ}C \\ High- and low-side FRFET switching (Note 4) $	Full Square			

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
IQCC	Quiescent V _{CC} Current	V _{CC} =15V, V _{IN} =0V	Applied between $V_{\mbox{\scriptsize CC}}$ and COM	-	-	160	μA
I _{QBS}	Quiescent V _{BS} Current	V _{BS} =15V, V _{IN} =0V	Applied between $V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	-	-	100	μA
UV _{CCD}	Low-side Undervoltage	V _{CC} Undervoltage Protection Detection Level		7.4	8.0	9.4	V
UV _{CCR}	Protection (Figure 6)	V _{CC} Undervoltage Protection Reset Level		8.0	8.9	9.8	V
UV _{BSD}	High-side Undervoltage	V _{BS} Undervoltage Protection Detection Level		7.4	8.0	9.4	V
UV _{BSR}	Protection (Figure 7)	V _{BS} Undervoltage Protection Reset Level		8.0	8.9	9.8	V
V _{IH}	ON Threshold Voltage	Logic High Level	Applied between IN and COM	3.0	-	-	V
V _{IL}	OFF Threshold Voltage Logic Low Level		-	-	0.8	V	
I _{IH}	Input Dice Current	$V_{IN} = 5V$	Applied between IN and COM	-	10	20	μA
۱ _{IL}	Input Bias Current	$V_{IN} = 0V$	Applied between IN and COM	-	-	2	μA

Note:

1. For the measurement point of case temperature ${\rm T}_{\rm C},$ please refer to Figure 3 in page 4.

2. BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each FRFET inside SPM[®]. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{DS} should not exceed BV_{DSS} in any case.

 t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 4 for the switching time definition with the switching test circuit of Figure 5.

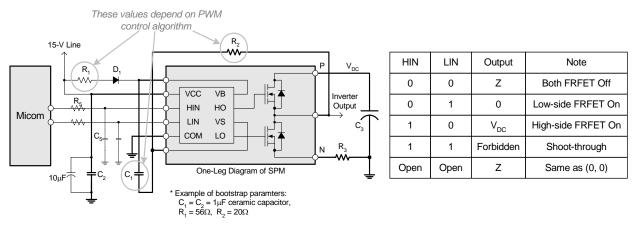
4. The peak current and voltage of each FRFET during the switching operation should be included in the safe operating area (SOA). Please see Figure 5 for the RBSOA test circuit that is same as the switching test circuit.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Packing Type	Quantity
FSB50550U	FSB50550U	SPM23-AD	_	_	15

Recommended Operating Conditions

Symbol	Parameter	Conditions	Value			Units
Symbol	Faranieter	Conditions	Min.	Тур.	Max.	Units
V _{PN}	Supply Voltage	Applied between P and N	-	300	400	V
V _{CC}	Control Supply Voltage	Applied between V_{CC} and COM	13.5	15	16.5	V
V _{BS}	High-side Bias Voltage	Applied between V_B and output(U, V, W)	13.5	15	16.5	V
V _{IN(ON)}	Input ON Threshold Voltage	Applied between IN and COM	3.0	-	V _{CC}	V
V _{IN(OFF)}	Input OFF Threshold Voltage		0	-	0.6	V
t _{dead}	Blanking Time for Preventing Arm-short	$V_{CC}\text{=}V_{BS}\text{=}13.5$ ~ 16.5V, $T_J \leq 150^\circ\text{C}$	1.0	-	-	μS
f _{PWM}	PWM Switching Frequency	$T_J \le 150^{\circ}C$	-	15	-	kHz

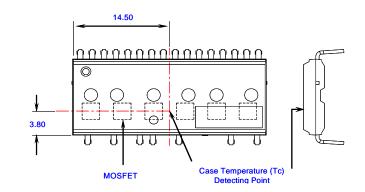


Note:

(1) It is recommended the bootstrap diode D1 to have soft and fast recovery characteristics with 600-V rating

- (2) Parameters for bootsrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- (3) RC coupling(R₅ and C₅) at each input (indicated as dotted lines) may be used to prevent improper input signal due to surge noise. Signal input of SPM[®] is compatible with standard CMOS or LSTTL outptus.
- (4) Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge voltage. Bypass capacitors such as C₁, C₂ and C₃ should have good high-frequency characteristics to absorb high-frequency ripple current.

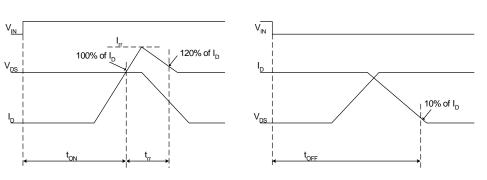
Figure 2. Recommended CPU Interface and Bootstrap Circuit with Parameters



Note:

Attach the thermocouple on top of the heatsink-side of SPM® (between SPM® and heatsink if applied) to get the correct temperature measurement.

Figure 3. Case Temperature Measurement





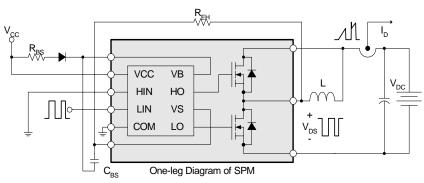
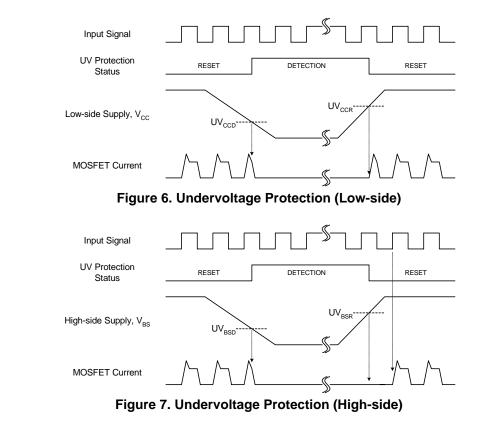


Figure 5. Switching and RBSOA(Single-pulse) Test Circuit (Low-side)



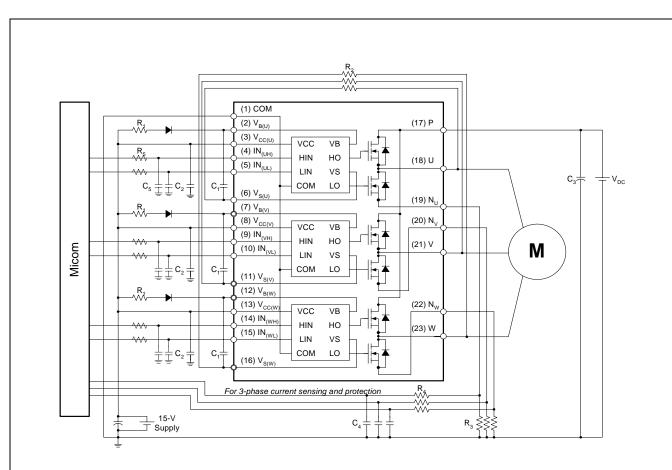
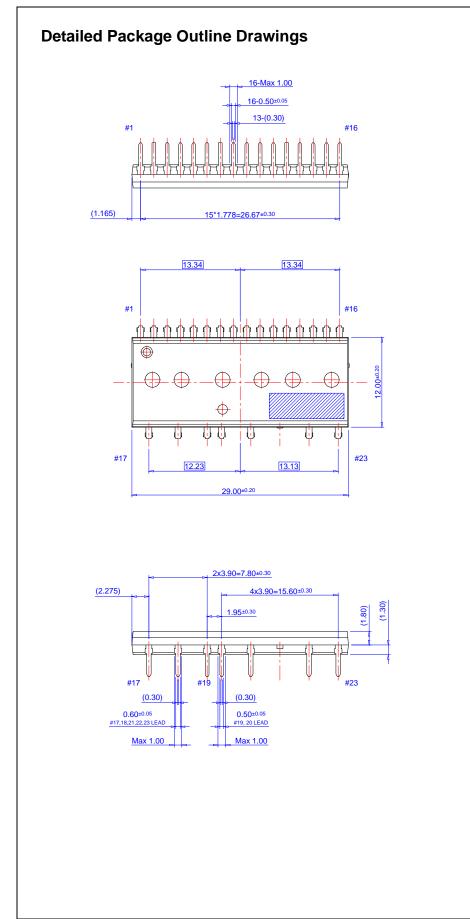
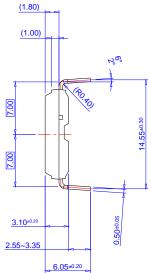


Figure 8. Example of Application Circuit





FAIRCHILD SEMICONDUCTOR TRADEMARKS The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks. AccuPower™ **FPST** PowerTrench[®] The Power Franchise[®] PowerXS™ Auto-SPM™ F-PFS™ p FRFET® Programmable Active Droop™ Build it Now™ franchise CorePLUS™ Global Power ResourceSM QFET TinyBoost™ QS™ CorePOWER™ Green FPS™ TinyBuck™ Quiet Series™ CROSSVOLT™ Green FPS™ e-Series™ TinyCalc™ RapidConfigure™ CTL™ G*m*ax™ TinyLogic® Current Transfer Logic™ GTO™ TINYOPTO™ **EcoSPARK**[®] IntelliMAX™ TinyPower™ EfficentMax™ ISOPLANAR™ Saving our world, 1mW/W/kW at a time™ TinyPWM™ EZSWITCH™* MegaBuck™ SmartMax™ TinyWire™ MICROCOUPLER™ SMART START™ . TriFault Detect™ MicroFET[™] SPM[®] TRUECURRENT™* MicroPak™ STEALTH™ µSerDes™ MillerDrive™ SuperFET™ $\mu_{_{Ser}}$ Fairchild® MotionMax™ SuperSOT™-3 Fairchild Semiconductor® Motion-SPM™ SuperSOT™-6 UHC FACT Quiet Series™ **OPTOLOGIC[®]** SuperSOT™-8 Ultra FRFET™ **FACT[®] OPTOPLANAR[®]** SupreMOS™ FAST®

FlashWriter^{®*} * Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

PDP SPM™

Power-SPM™

DISCLAIMER

FastvCore™

FETBench™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

SyncFET™

Sync-Lock™

GENERAL

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

bwer

UniFET™

VisualMax™

VCX™

XS™

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 141

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC